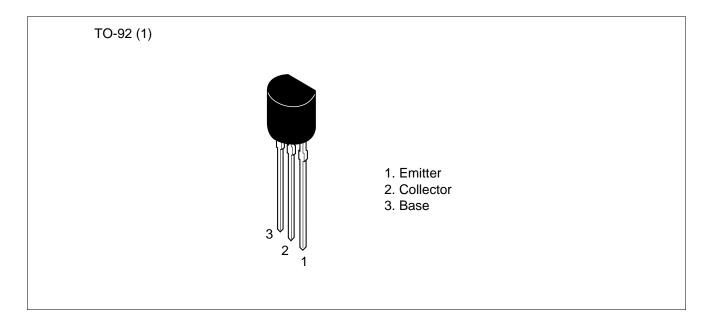
Silicon PNP Epitaxial

# **HITACHI**

### Application

- Low frequency amplifier
- Medium speed switching

#### **Outline**



### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	-50	V
Collector to emitter voltage	V <sub>CEO</sub>	-50	V
Emitter to base voltage	V <sub>EBO</sub>	-4	V
Collector current	I <sub>c</sub>	-0.5	A
Collector power dissipation	P <sub>c</sub>	0.4	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

#### **Electrical Characteristics** (Ta = 25°C)

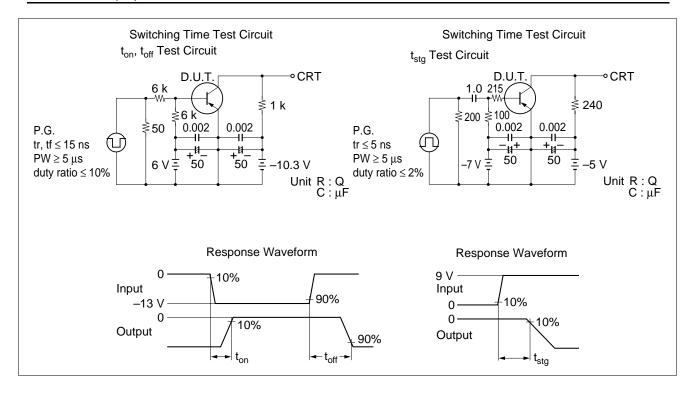
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	<del>-</del> 50	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	_	_	V	$I_{C} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-4	_	_	V	$I_{E} = -10 \mu A, I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_		-0.5	μΑ	$V_{CB} = -20 \text{ V}, I_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_	_	-0.5	μΑ	$V_{EB} = -3 \text{ V}, I_{C} = 0$
Base to emitter voltage	$V_{BE}$	_	-0.64	_	V	$V_{EB} = -3 \text{ V}, I_{C} = -10 \text{ mA}$
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	-0.2	-0.6	V	$I_{\rm C} = -150 \text{ mA}, I_{\rm B} = -15 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	-0.87	_	V	$I_{\rm C} = -150 \text{ mA}, I_{\rm B} = -15 \text{ mA}^{*2}$
DC current transfer ratio	h <sub>FE</sub> *1	60	_	320		$V_{CE} = -3 \text{ V}, I_{C} = -10 \text{ mA}$
	h <sub>FE</sub>	10	_	_		$V_{CE} = -3 \text{ V}, I_{C} = -500 \text{ mA}^{*2}$
Gain bandwidth product	f <sub>T</sub>	_	120	_	MHz	$V_{CE} = -3 \text{ V}, I_{C} = -10 \text{ mA}$
Turn on time	t <sub>on</sub>	_	0.3		μs	V <sub>CC</sub> = -10.3 V
Turn off time	t <sub>off</sub>		0.6		μs	$I_{\rm C} = 10 I_{\rm B1} = -10 I_{\rm B2} = -10  \rm mA$
Storage time	t <sub>stg</sub>	_	0.4	_	μs	$V_{CC} = -5 \text{ V},$ $I_C = I_{B1} = I_{B2} = -20 \text{ mA}$

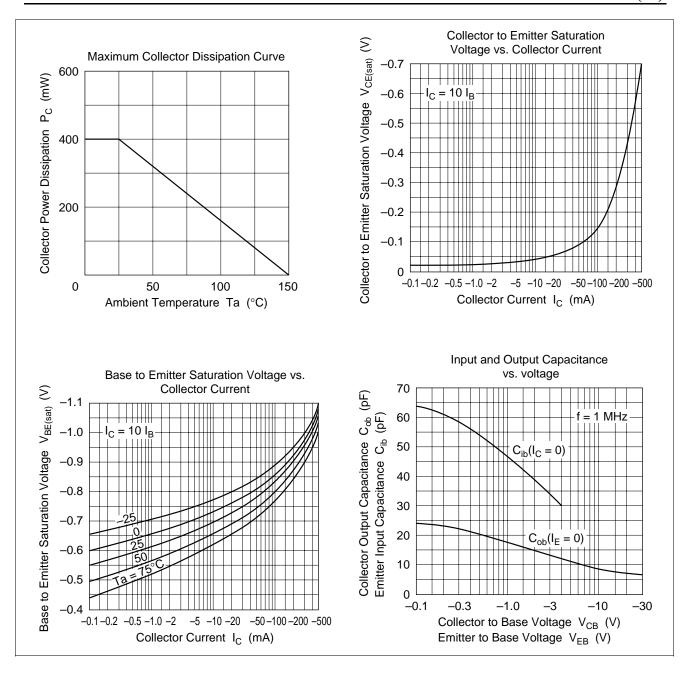
Notes: 1. The 2SA673A(K) is grouped by  $h_{\rm FE}$  as follows.

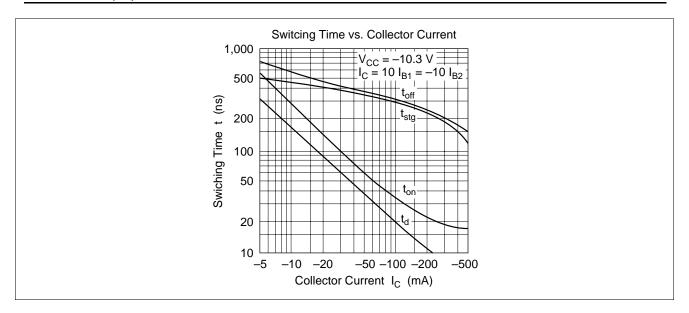
2. Pulse test

В	С	D
60 to 120	100 to 200	160 to 320

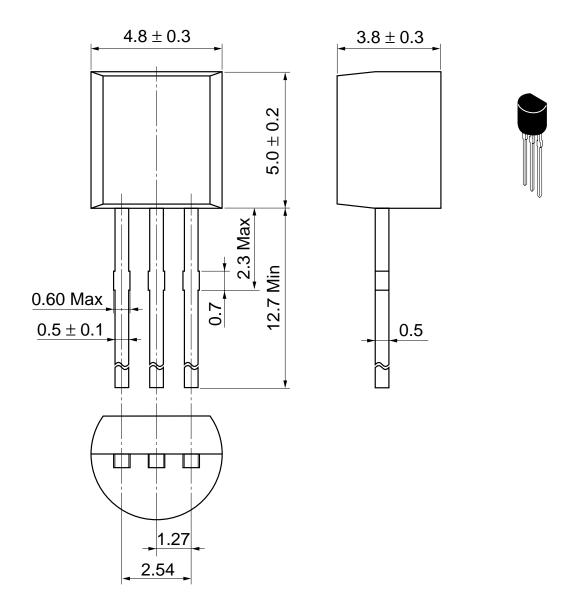
See 2SA673A except for the above – mentioned characteristic curves.







Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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